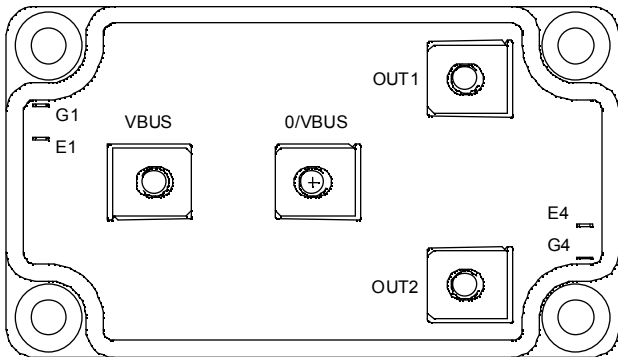
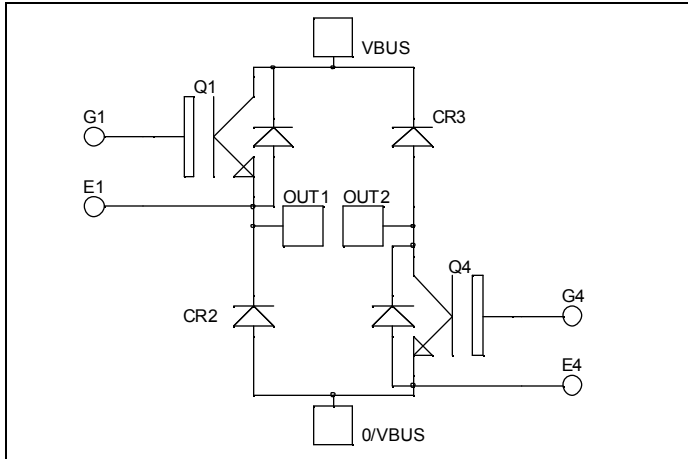


## Asymmetrical - Bridge NPT IGBT Power Module

$V_{CES} = 1200V$   
 $I_C = 150A @ T_c = 80^\circ C$



### Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CESat}$
- Low profile
- RoHS compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	200
		$T_c = 80^\circ C$	150
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	300
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	961
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	300A @ 1200V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	$T_j = 25^\circ\text{C}$			350	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$			600	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 150\text{A}$	$T_j = 25^\circ\text{C}$		3.2	3.7	V
			$T_j = 125^\circ\text{C}$		3.9		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 5\text{mA}$	4.5		6.5	V	
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$			$\pm 500$	nA	

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}$ $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		10.2		nF	
$C_{oes}$	Output Capacitance			1.4			
$C_{res}$	Reverse Transfer Capacitance			0.75			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 150\text{A}$ $R_G = 5.6\Omega$		120		ns	
$T_r$	Rise Time			50			
$T_{d(off)}$	Turn-off Delay Time			310			
$T_f$	Fall Time			20			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 150\text{A}$ $R_G = 5.6\Omega$		130		ns	
$T_r$	Rise Time			60			
$T_{d(off)}$	Turn-off Delay Time			360			
$T_f$	Fall Time			30			
$E_{on}$	Turn-on Switching Energy	$V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 150\text{A}$ $R_G = 5.6\Omega$	$T_j = 125^\circ\text{C}$		18		mJ
$E_{off}$	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$		8		

**Diode ratings and characteristics**

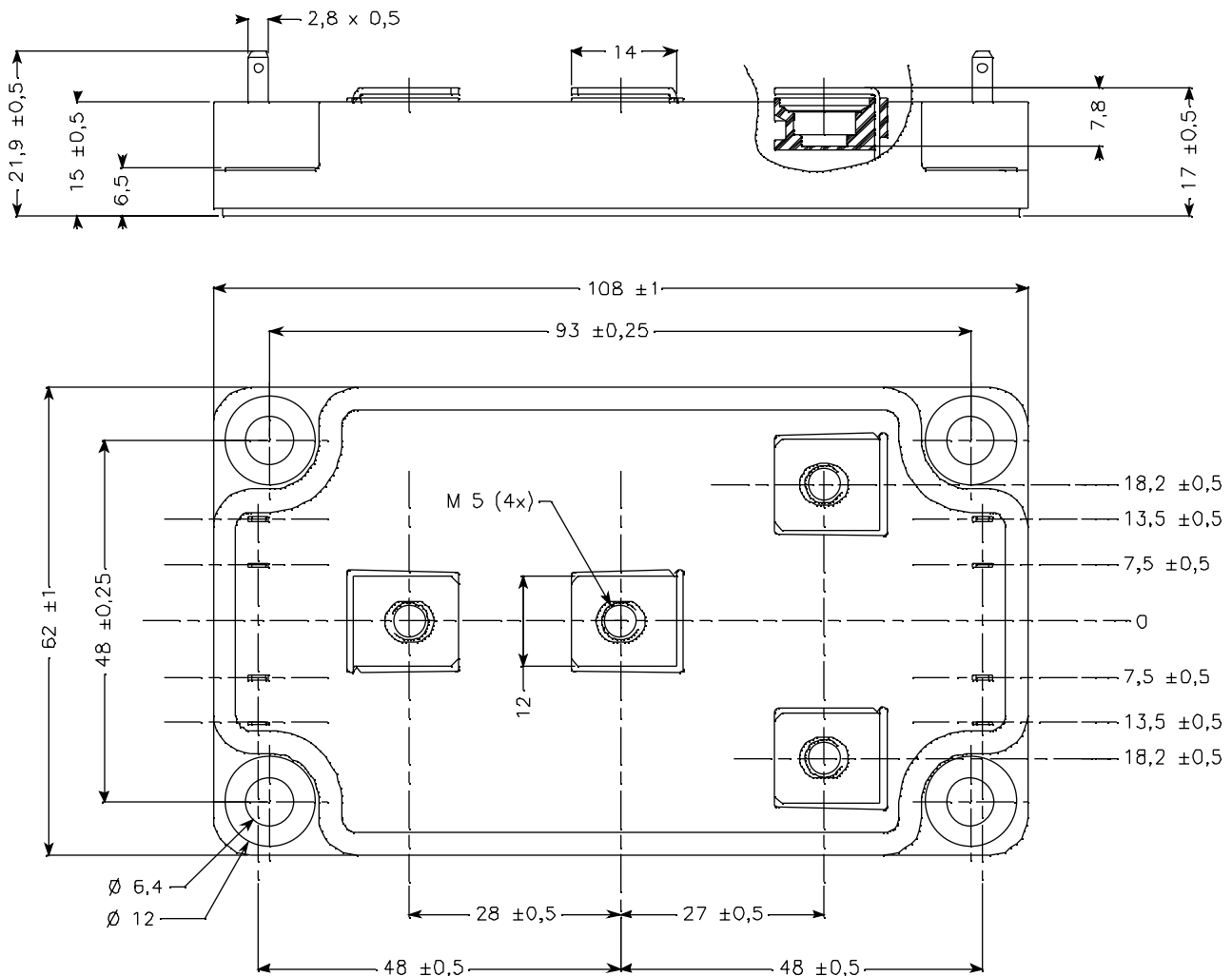
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V	
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$			350	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$			600	
$I_F$	DC Forward Current			200		A	
$V_F$	Diode Forward Voltage	$I_F = 200\text{A}$		2	2.5	V	
		$I_F = 400\text{A}$		2.3			
		$I_F = 200\text{A}$	$T_j = 125^\circ\text{C}$		1.8		
$t_{rr}$	Reverse Recovery Time	$I_F = 200\text{A}$ $V_R = 800\text{V}$ $di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		420	ns	
			$T_j = 125^\circ\text{C}$		520		
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		2.5	$\mu\text{C}$	
			$T_j = 125^\circ\text{C}$		10.7		

## Thermal and package characteristics

*Symbol Characteristic*

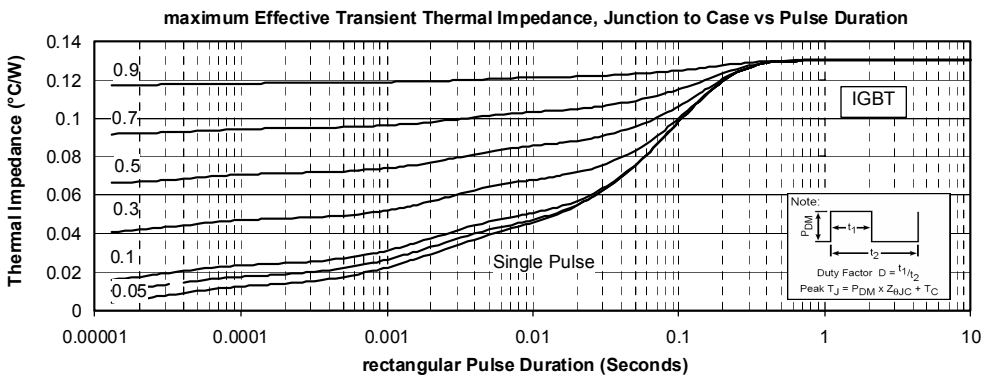
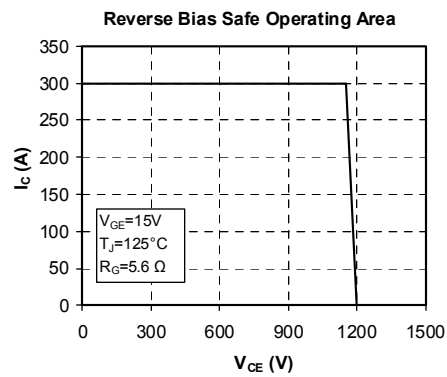
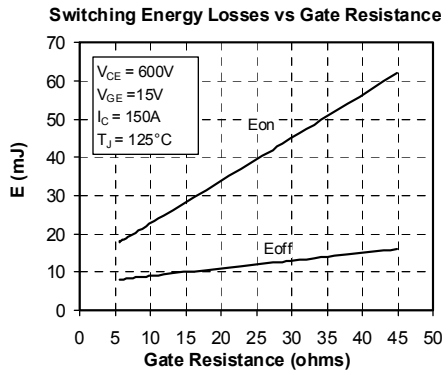
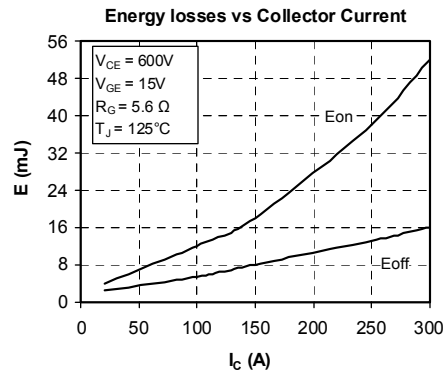
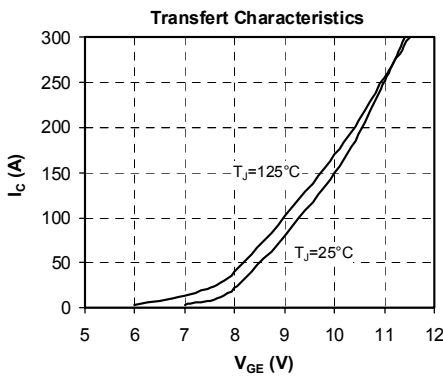
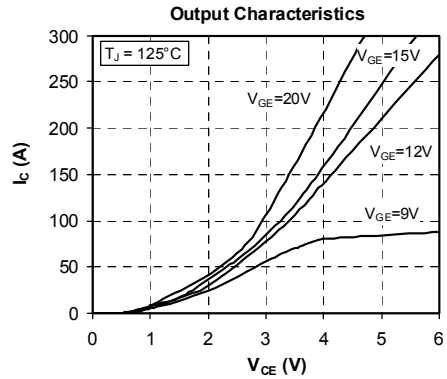
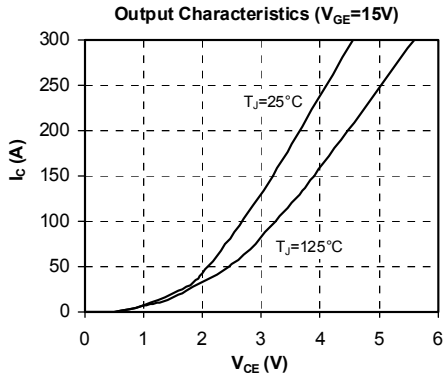
		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
$R_{thJC}$	Junction to Case Thermal Resistance	IGBT		0.13	°C/W	
		Diode		0.32		
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{isol}<1$ mA, 50/60Hz	2500			V	
$T_J$	Operating junction temperature range	-40		150	°C	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight			280	g	

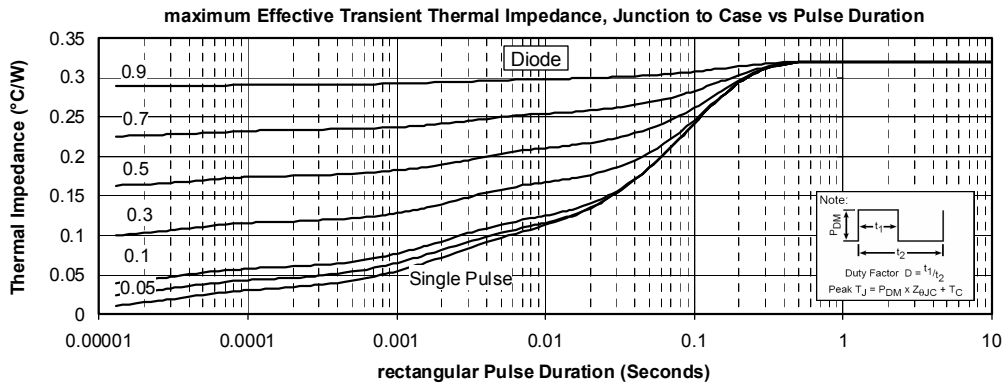
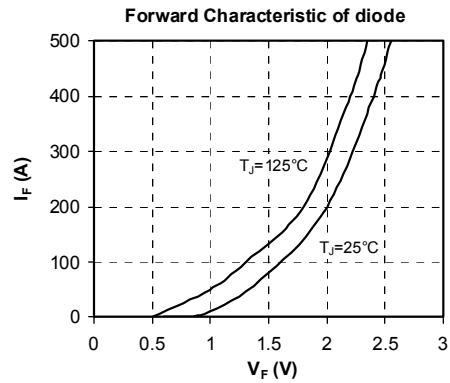
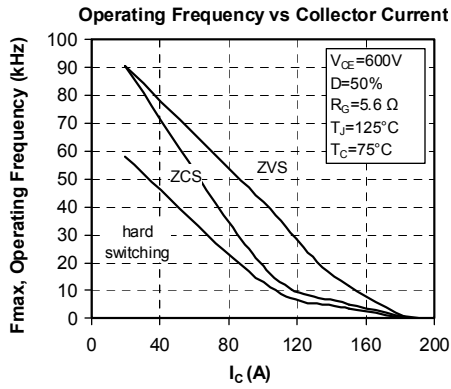
## SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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